

Docket No.: 67161-073

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of :
Tetsuya NITTA, et al. :
Serial No.: : Group Art Unit:
Filed: July 24, 2003 : Examiner:
For: INTEGRATED SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING
THEREOF

INFORMATION DISCLOSURE STATEMENT

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The relevance of each Japanese Patent Application is discussed in the present specification.

Serial No.:

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY



Stephen A. Becker

Registration No. 26,527

600 13th Street, N.W.
Washington, DC 20005-3096
(202) 756-8000 SAB:km
Facsimile: (202) 756-8087
CUSTOMER NUMBER 20277
Date: July 24, 2003

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)		ATTY. DOCKET NO. 67161-073		SERIAL NO.			
		APPLICANT Tetsuya NITTA, et al.					
		FILING DATE July 24, 2003		GROUP			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number & Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		JP 6-318561	11/15/1994	HAYASHI		abstract	
		JP 11-238806	08/31/1999	KITADE		abstract	
		JP 11-111855	04/23/1999	HIGUCHI		abstract	
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		LUDIKHUIZE, et al. "Extended (180V) Voltage in 0.6µm Thin-Layer-SOI A-BCD3 Technology on 1µm BOX for Display, Automotive & Consumer Applications" Proceedings of the 14th International Symposium on Power Semiconductor Devices & ICS, Santa Fe, NM (June 4-7, 2002) pp.77-80.					
EXAMINER				DATE CONSIDERED			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered.

Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.